

Product Overview

NSS20601CF8: Low $V_{CE(sat)}$ Transistor, NPN, 20 V, 8.0 A

For complete documentation, see the data sheet.

Low $V_{CE(sat)}$ Bipolar Transistors are miniature surface mount devices featuring ultra low saturation voltage $V_{CE(sat)}$ and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Features

- High Current, Low $V_{CE(sat)}$, ESD Robust, High Current Gain, High Cut Off Frequency, Low Profile Package, Linear Gain (Beta)

Benefits

- Improved Circuit Efficiency, Decreased Battery Charge Time, Reduce component count, High Frequency Switching, Smaller Portable Product, No distortion

Applications

- Load Switching, Battery Charging, External Pass Transistor, DC/DC Converter, Complimentary Driver, Current Extention & Low Drop Out Regulation, Cathode Florescent Lamp drive, Peripheral Driver - LEDs, Motors, Relays

Part Electrical Specifications

Product	Compliance	Status	Polarity	Type	$V_{CE(sat) Max}$ (V)	I_C Cont. (A)	$V_{CEO Min}$ (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(on)}$ (V)	$h_{FE Min}$	$h_{FE Max}$	f_T Min (MHz)	$P_{TM Max}$ (W)	Package Type
NSS20601CF8T1G	Pb-free Halide free	Active	NPN	Low $V_{CE(sat)}$	0.065	6	20	20	6	0.9	0.9	200	-	140	1.4	Chip FET-8

For more information please contact your local sales support at www.onsemi.com.

Created on: 9/20/2019